Elektronische Bauelemente

CZD1386

-5 A, -30 V

PNP Epitaxial Silicon Transistor

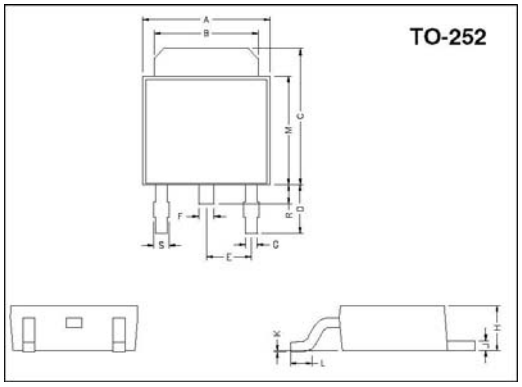
DESCRIPTION

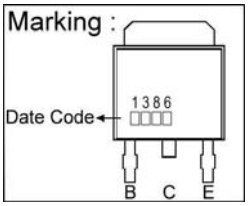
The CZD1386 is designed for low frequency applications.

FEATURES

- Low $V_{CE(sat)}$ = -0.55V(Typ.) (I_C/I_B = -4 A/ -0.1 A)
- Excellent DC current gain characteristics

PACKAGE DIMENSIONS





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 Ref.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

ABSOLUTE MAXIMUM RATINGS at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-5	A
*Collector Current (Pulse)	I_C	-10	A
Total Power Dissipation	Pc	20	W
Junction, Storage Temperature	T_J, T_{STG}	+150, -55 ~ +150	℃

CHARACTERISTICS at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-30	-	-	V	I_C=-50uA
BVCEO	-20	-	-	V	I_C=-1mA
BVEBO	-6	-	-	V	I_E=-50uA
ICBO	-	-	-500	nA	V_{CB}=-20V
IEBO	-	-	-500	nA	V_{EB}=-5V
*VCE(sat)	-	-	-1	mV	I_C=-4A, I_B=-0.1mA
*hFE	82	-	580		V_{CE}=-2V, I_C=-0.5mA
fT	-	120	-	MHz	V_{CE}=-6V, I_E=50mA, f=30MHz
Cob	-	60	-	pF	V_{CB}=-20V, I_E=0, f=1MHz

* Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%

CLASSIFICATION OF $h_{FE}1$

Rank	P	Q	R	E
Range	82 - 180	120 - 270	180 - 390	370 - 580

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CHARACTERISTIC CURVES